

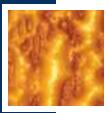
Today's SPM in Nanotechnology

An introduction for Advanced Applications

Qun (Allen) Gu, Ph.D., AFM Scientist, Pacific Nanotechnology

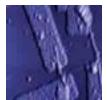
IEEE Bay Area Nanotechnology Council, August, 2007





Content

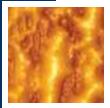






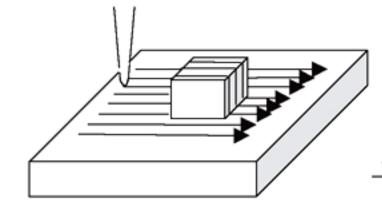
- AFM fundamentals: Principle, instrument, applications
- Field Modes
 - EFM
 - KPM
 - MFM
- Shark Modes (C-AFM, I-V)
- Lithography
 - LAO
 - Scratch
 - DPN

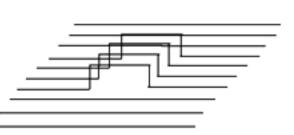




What is an SPM

 An SPM is a mechanical imaging instrument in which a small, < 10 nm in radius, probe is scanned over a surface. By monitoring the motion of the probe, the surface topography and/or surface physical properties are measured with an SPM.





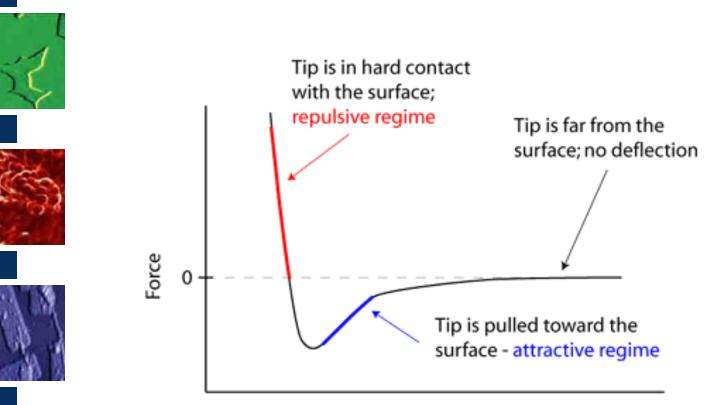








Forces



Probe Distance from Sample (z distance)

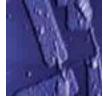






AFM System









Computer

Software for gathering and processing images resides on the computer.

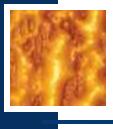
Electronic Controller

Generates electronic signals that control all functions in the stage

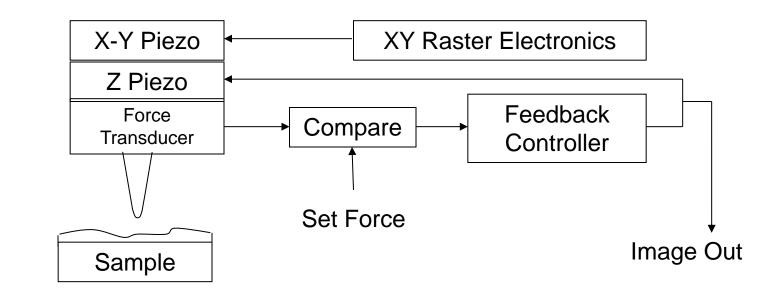
Stage

Scanner (laser, PD, PZ), Optical Microscope, sample stage.





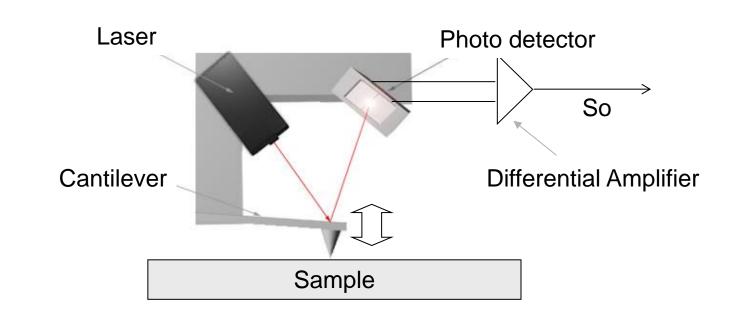
AFM System







AFM Light Lever





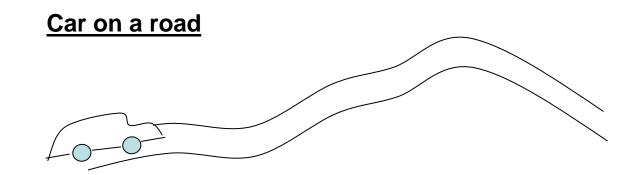
When the cantilever moves up and down, the position of the laser on the photo detector moves up and down.





Feedback Control

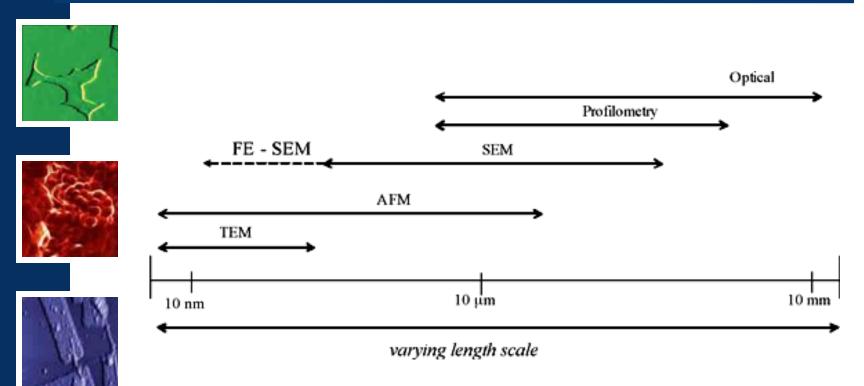
- A control system which monitors its effect on the system it is controlling and modifies its output.
- Measure, Compare, Update







Comparison





Non-destructive; 3D Magnification; Ambient air; Surface physical property





AFM Applications



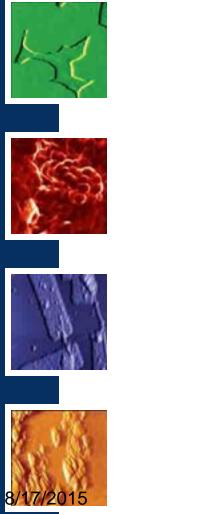
- Life Sciences
 - Cells, Bio-molecules, Biomaterials
- Material Sciences
 - Semiconductors, Ceramics, Polymers
- High Technology
 - Data Storage, Optics, Semiconductors, Biotech.
- Low Technology
 - Paper, Steel, Plastics, Automobile

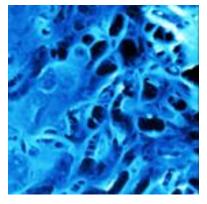


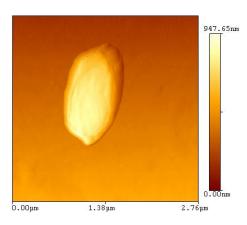


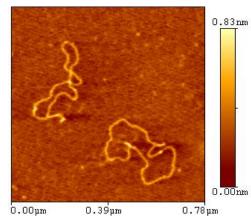


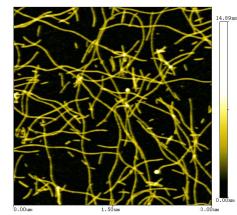
Life Sciences









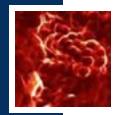






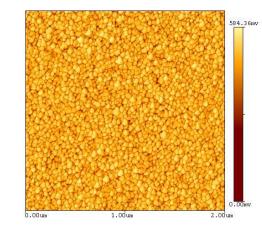
Material Sciences

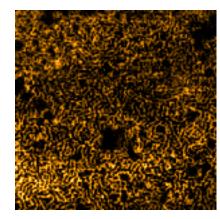


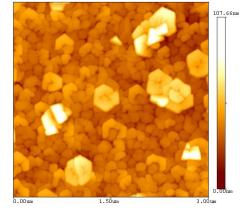


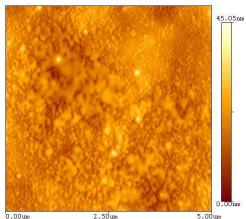




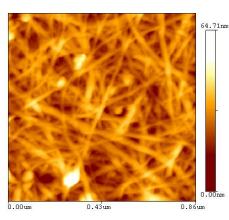


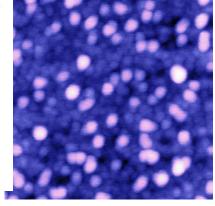






5.00um

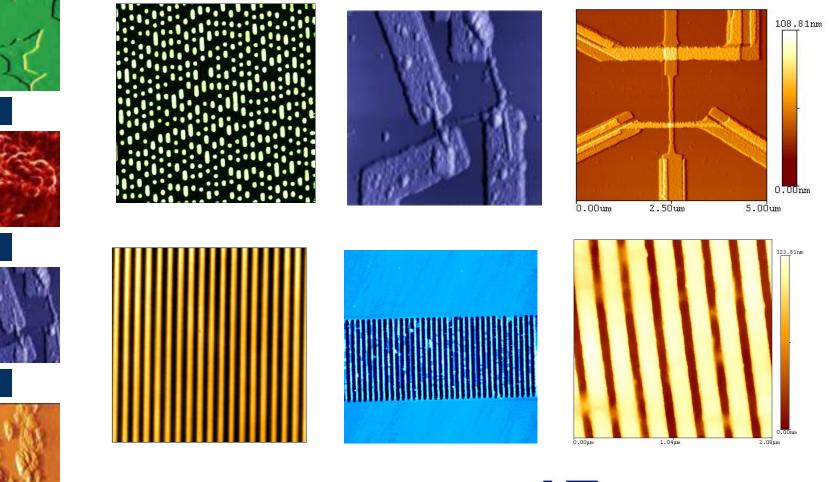








High Technology

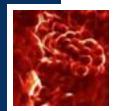






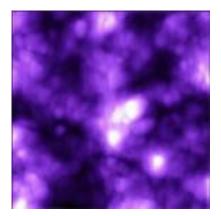
Low Technology

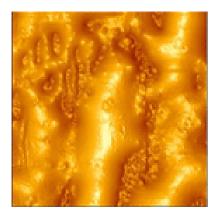


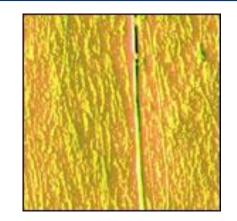


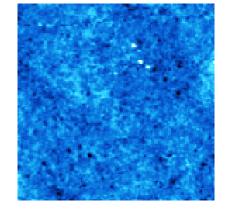


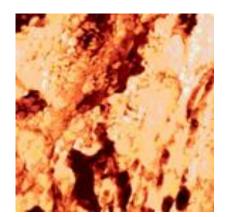


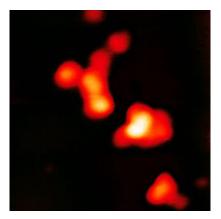








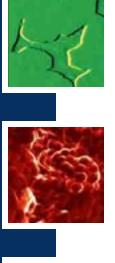


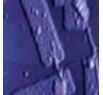






AFM Modes: Advanced Applications



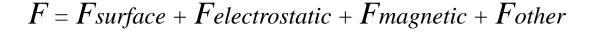


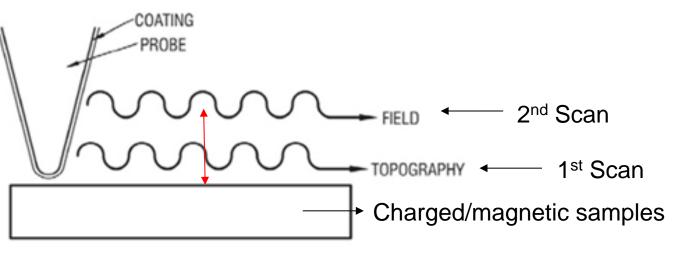


- Field Modes
 - KPM/EFM
 - Magnetic Force
- Electrical Modes (Shark)
- Lithography
 - LAO
 - Scratching
 - DPN
- Material Sensing Modes
 - Lateral Force
 - Vibrating Phase
- Mechanical
 - Force/Distance
 - Indenting
- Liquid



Field Modes





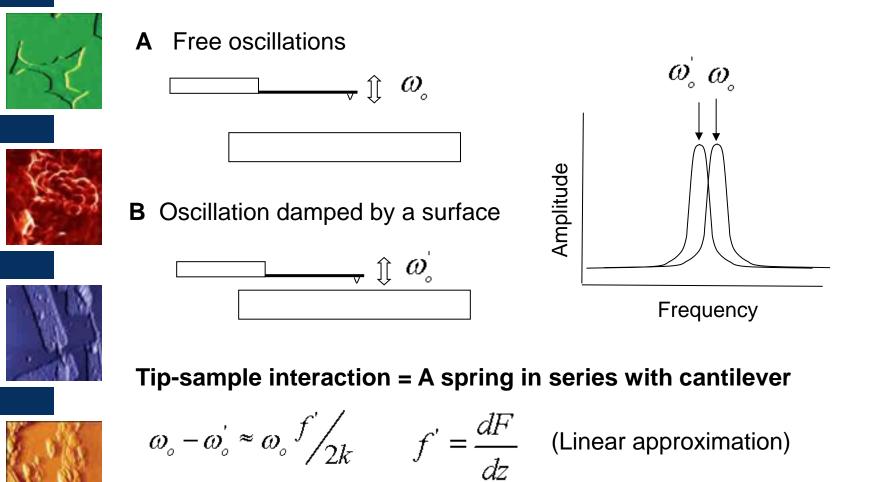


- Electrostatic force/magnetic force interaction (> tens of nm)
- Qualitative/Quantitative
- Resolution depends on sample, probe coating





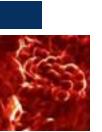
Probe/Surface Interaction



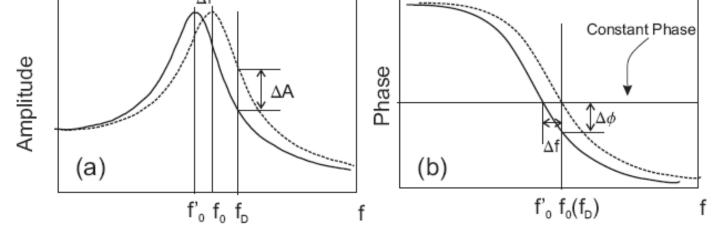




INSTRUMENTATION



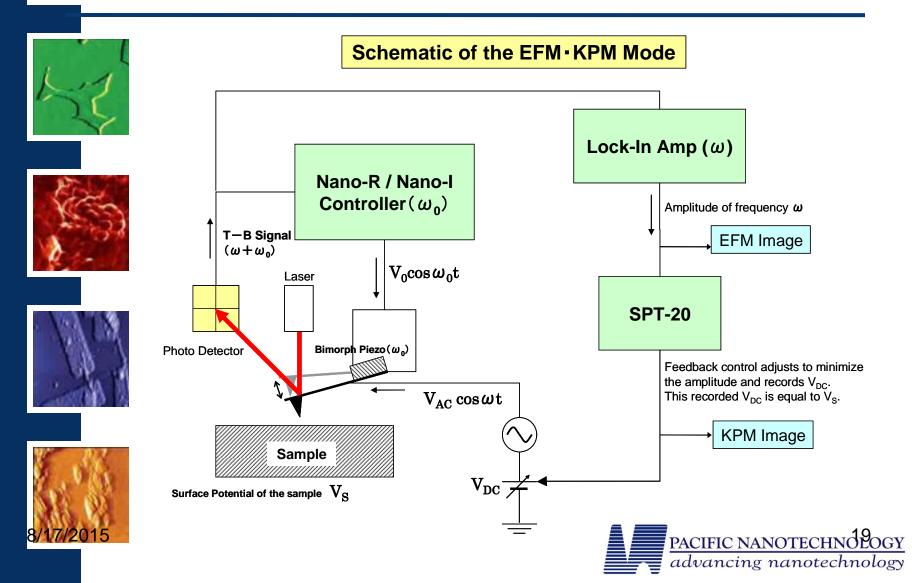




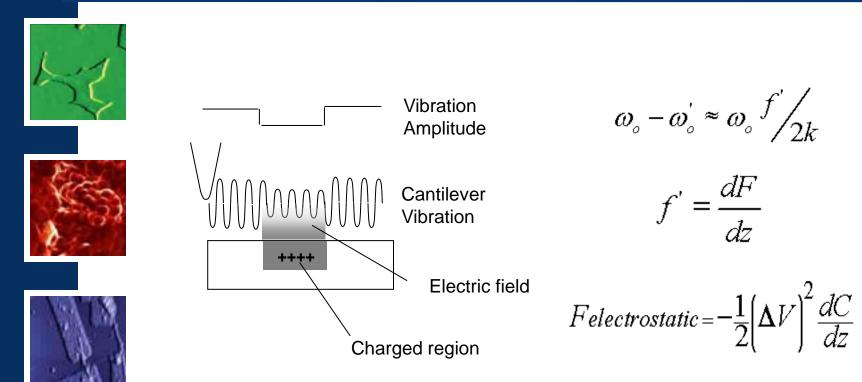
- **1.** Lock-in technique: at *constant fD*, cantilever Δf results in ΔA (a) and $\Delta \phi$ (b), which can be interpreted as a force signal. (No FB)
- 2. Frequency Modulation (servo controller): Measure Δf : at the constant phase (phase lag is zero in a phase locked loop).







EFM





Calculate the change in the resonant frequency(ω): Use Equations for fields above a surface and calculate the derivative of the field.

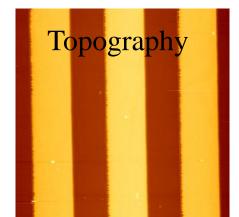


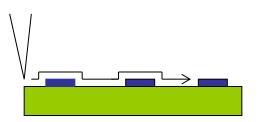


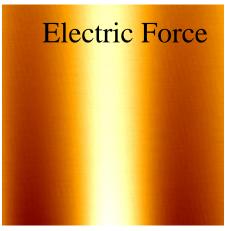
Electric Forces (EFM)

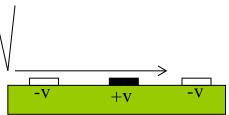




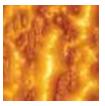












KPM

$$F_Z = -\frac{1}{2} \frac{\partial C}{\partial z} (V_{\rm S} + V_{\rm DC} + V_{\rm AC} \cos \omega_{\rm m} t)^2$$

= $-\frac{1}{2} \frac{\partial C}{\partial z} \{ (V_{\rm S} + V_{\rm DC})^2 + 2 (V_{\rm S} + V_{\rm DC}) V_{\rm AC} \cos \omega_{\rm m} t + V_{\rm AC}^2 \cos^2 \omega_{\rm m} t \}$

Vs: Contact potential difference or work function difference

- DC component: static attractive force between electrodes (topo)
- $\boldsymbol{\omega}$ component: a force between charges induced by AC field (KPM)
- 2 ω component: a force induced to capacitors only by AC voltage (SCM)

8/17/2015

Lock-in Amp detects the signal at ω , feedback control minimizes this component by adjusting V_{DC}, so V_S+V_{DC} = 0





EFM/KPM

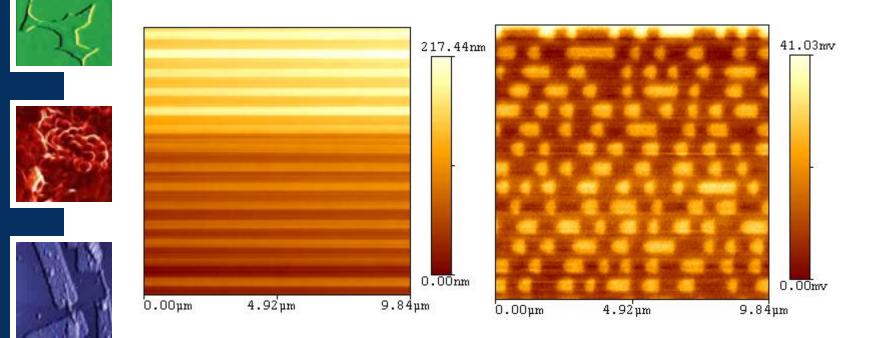


Surface potential distribution Capacitance (C-z, C-V) Polarization of adsorbed molecules Polarization or piezo effect of ferroelectric Charge distribution Carrier distribution in semiconductor Local work function others





EFM/KPM



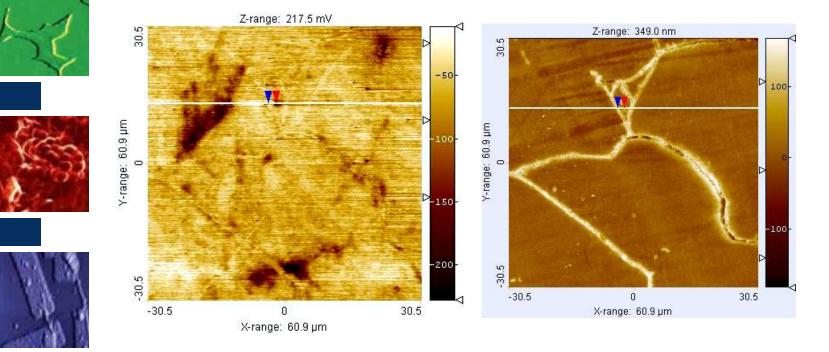


10X10 um topography and KPM images of a DVD-RW surface





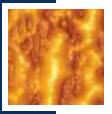
Corrosion Study



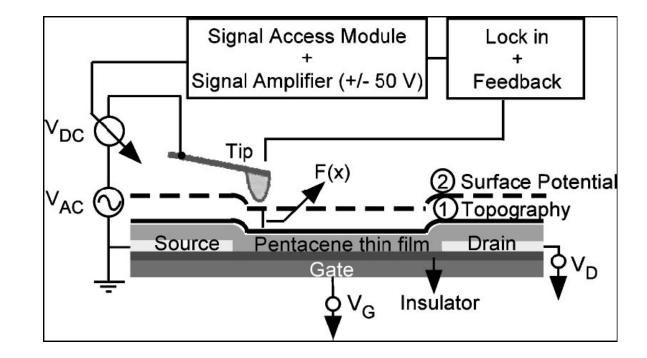


Surface potential mapping for a metal alloy surface: enhanced corrosion (higher cathodic reaction) observed in the boundaries.





Semiconductor



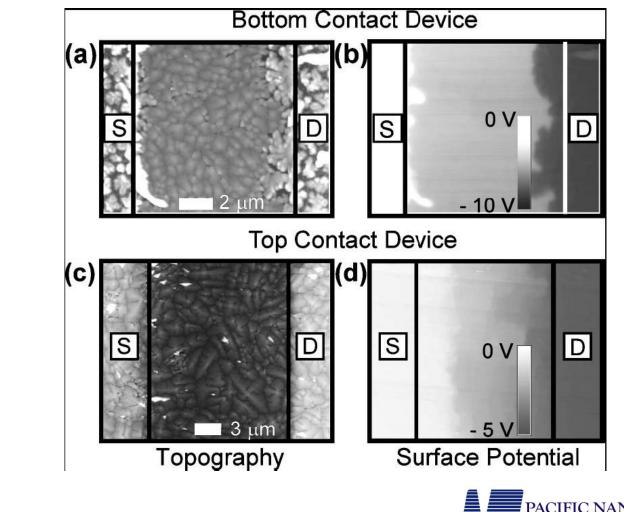
Puntambekar et al., Appl. Phys. Lett., Vol. 83, No. 26, 29 December 2003



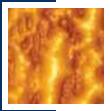




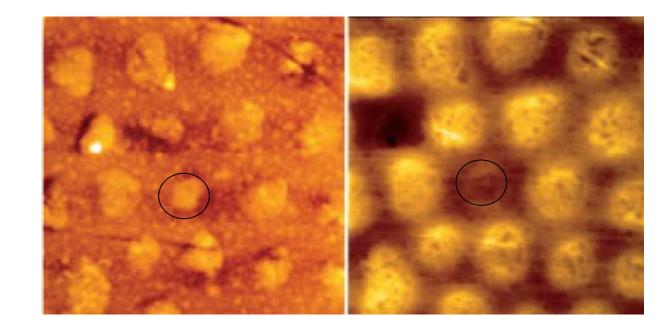
Semiconductor







Nanomaterials



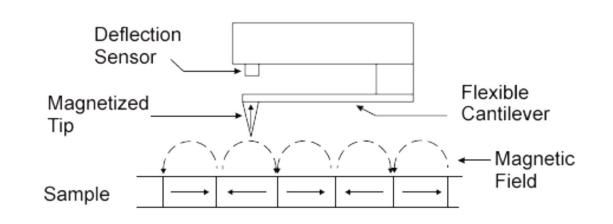


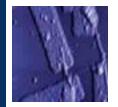
Nanowires embedded in alumina matrix. (Right) EFM images show the electrical discontinuity of the nanowires.

C. A. Huber; Science, 263, 1994), pp. 800-802.









A magnetically sensitive cantilever interacts with the magnetic stray field of the sample. Resulting changes in the status of the cantilever are measured by the deflection sensor, and recorded to produce an image.





$$F = Fmag + Felec + Fvan$$

 $Fvan = A_H R/6z^2$ $Felec = \pi \varepsilon V^2 R/z^2$

R=10 nm, Z=50 nm, F'elec, F'van ~ 10^{-6} N/m

F'mag ~ $1/(a+z)^2$ a: domain width; z: distance

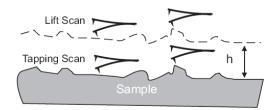
Sharp tip and small V, F'elec F'van $\leq F'mag$ (at Z > 20 nm)

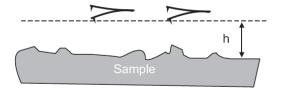












Constant frequency mode:

Maintain the frequency by adjusting z Topography convolution; AC+DC Felec as servo force

Lift-mode:

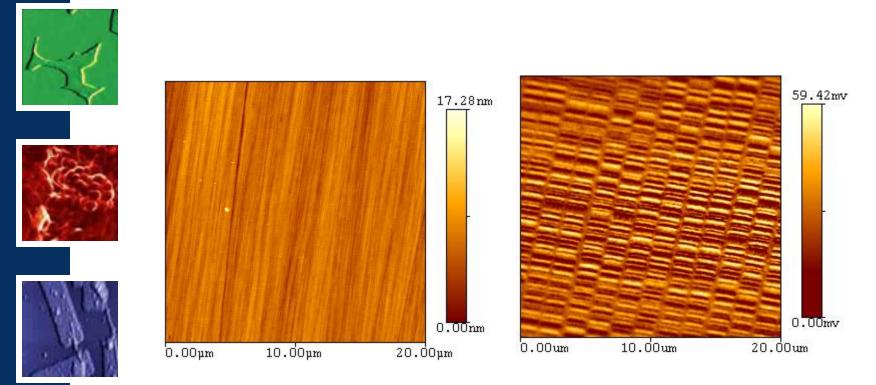
Monitoring fr or the phase shift during 2nd pass

Constant height:

Applying small bias to compensate Felec by work function difference; Highest S/N (no FB noise)





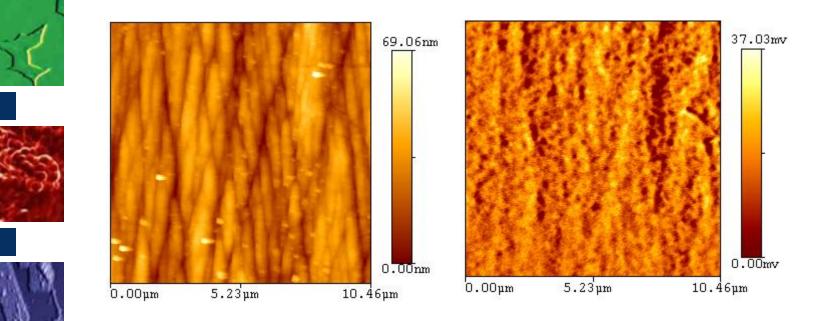




A topography (left) and MFM image (right) for a hard disk.





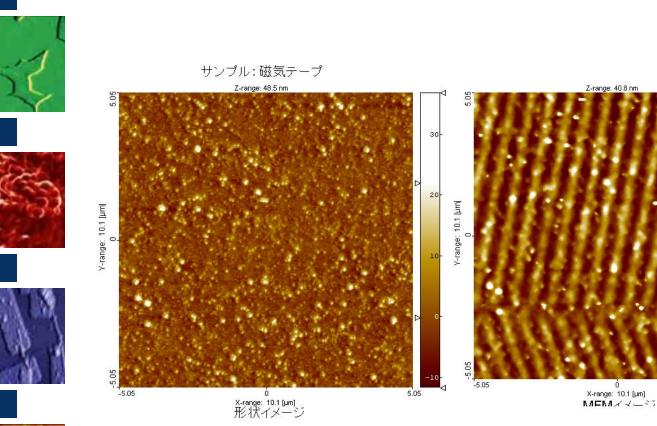




A topography (left) and MFM image (right) for a degassed hard disk. MFM image acquired by raising the magnetic tip ~80 nm above the surface. The bit microstructures were never found on this sample surface.







A topography (left) and MFM image (right) for a Magnetic recording tape



20

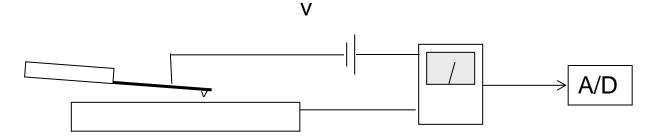
10

5.05



SHARK Mode

- Monitor Current Between Tip and Sample while scanning in contact mode
- Measure current map and Topography Simultaneously

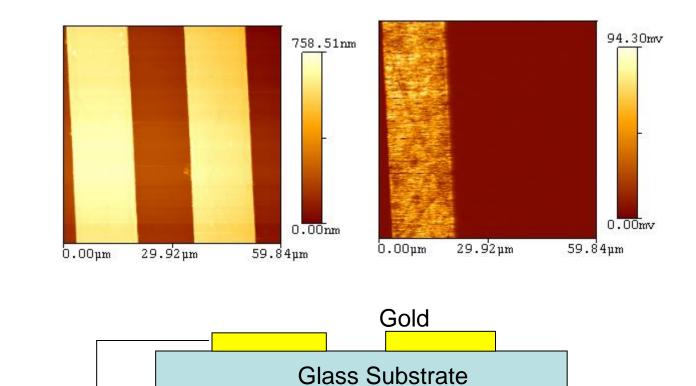








SHARK Example



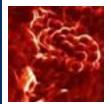






Electrical Test







► I-¥ Measure ×
Setting Measure
Position Setpoint
× 0.751 (um) 0 ÷ (m∨) 24.72 mm
Y 0.386 (um)
Result From -150 ↔ (mV)
Title Result delta 5 (mV)
Unit mA Conv. 1E-08 Min. Hold 2000 (mS)
Ratio

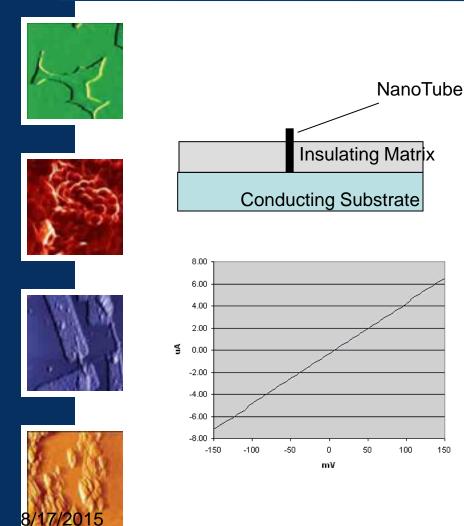


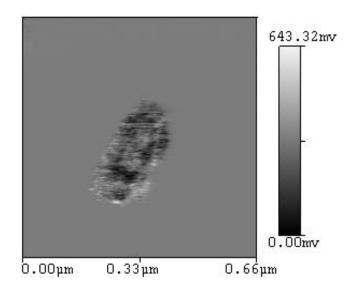
LPM Software allows probing the sample; SP, Voltage ramping, holding time





SHARK Example

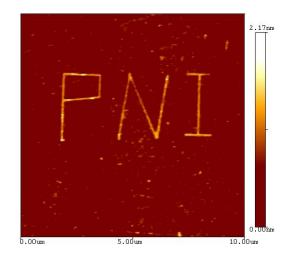








Nano-Lithography





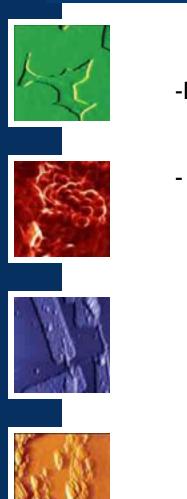
- -Change surface chemical composition
- -Deposit materials on a surface
- -Physically scratch surface

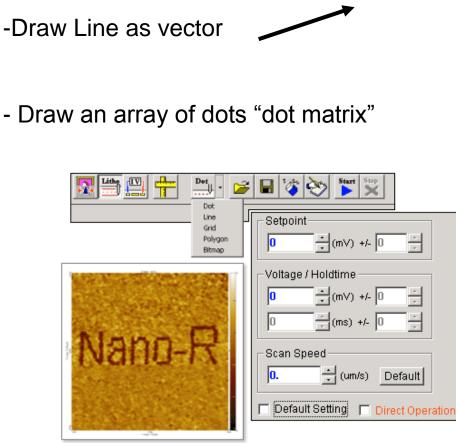






Nano-Lithography

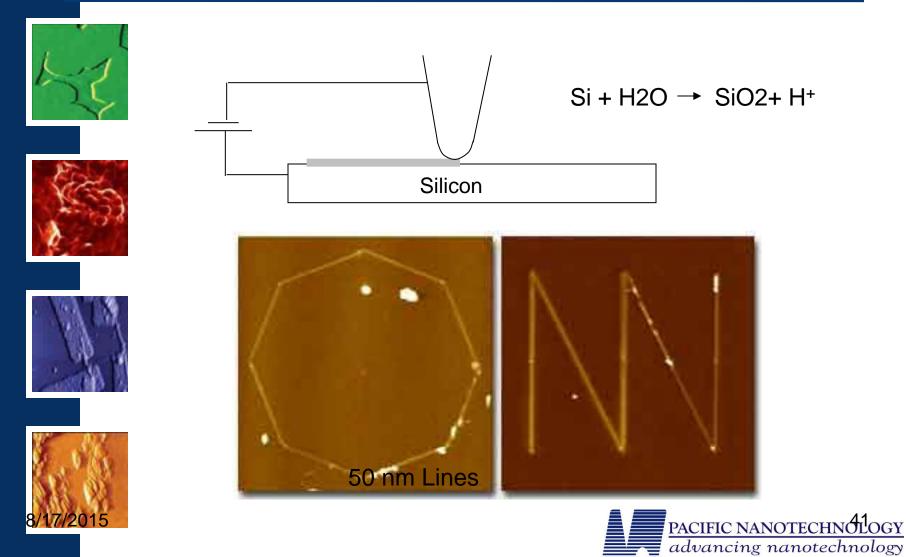






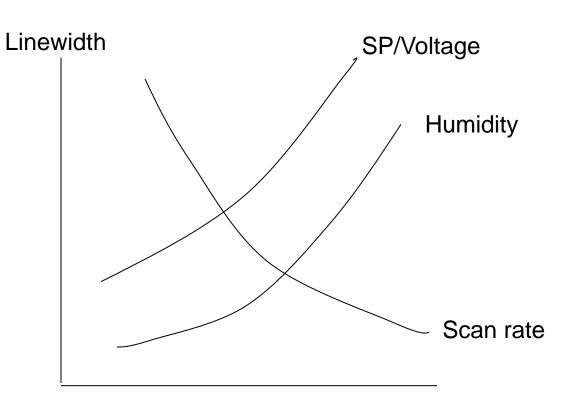


Local Anodic Oxidation





Local Anodic Oxidation

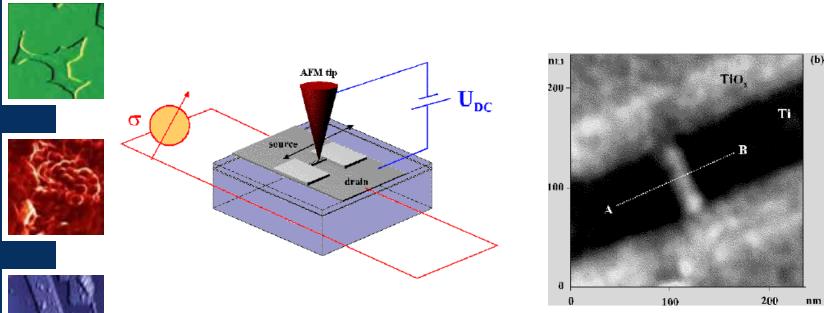








Local Anodic Oxidation





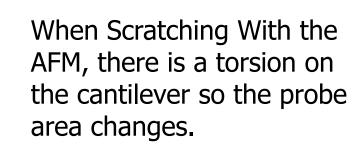


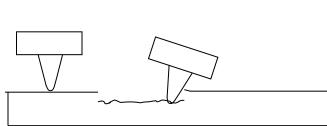
The formation of a single (tunneling) barrier within a thin metal film is shown. The tip repeatedly scans along a single line, monitoring the conductance through the device while oxidising. The image shows the 70nm wide metallic wire(black), defined by AFM induced oxide barrier, 21 nm wide.

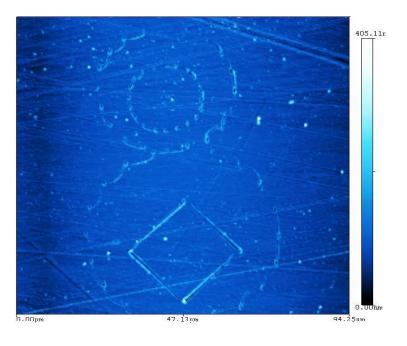




Scratching





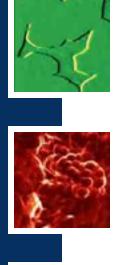


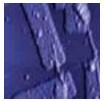


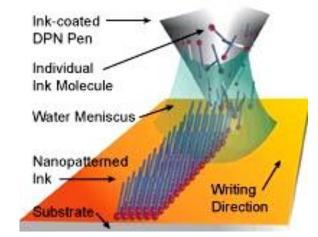


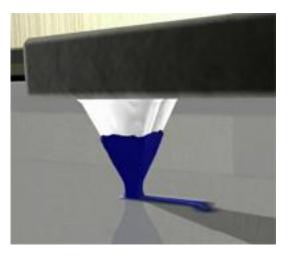


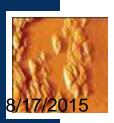
DIP-PEN NANOLITH





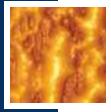




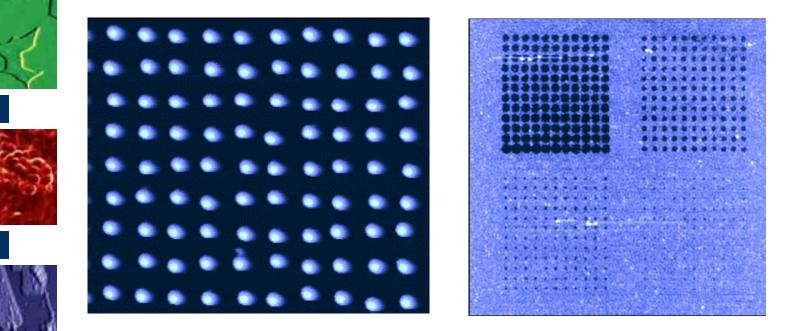


Transfer ink materials (small molecules) onto substrate in a pre-defined pattern





DIP-PEN NANOLITH





(Left) amino-modified polystyrene particles onto carboxylic acid alkanethiol (-) template. (Right) Opposite electrostatic assembly of citrate-stabilized gold nanoparticles onto carboxylic acid alkanethiol (-) surrounding a hydrophobic, uncharged dot array (ODT).





DIP-PEN NANOLITH



High Resolution and Accuracy: 14 nm linewidths, 5 nm spatial resolution; Automated registry

Versatile Chemical and Material Flexibility: Alkylthiols (e.g. ODT & MHA), Fluorescent dye, Silazanes, Alkoxysilanes, Conjugated polymer, DNA, Proteins, Sols, Colloidal particles, Metal salts

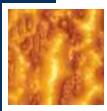


Simple Operation and Experimental Procedures: Can deposit direct-write, without need for resists; Operates in ambient conditions (no UHV); Patterning and imaging by the same instrument.



Patterning and imaging routines are automated via InkCAD; parallel pen arrays scale to 52 parallel pens; 2D nano PrintArrays[™] in development: 2D arrays of 55,000 pens.





Summary



AFM is a Hot Instrument in nanotechnology applications

- High Resolution: a few nm X/Y, A in Z
- Versatile: Measure electrical/magnetic field, tens of nm

I-V Curve measurement, conductive mapping

Nanolithography (LAO/DPN); Force measurement

- Non-destructive, Ambient/water environments, affordable
- Weakness: Limited Z, Low speed, ...

